Excellent Integrated System Limited

Stocking Distributor

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Rohm Semiconductor RHK003N06T146

For any questions, you can email us directly: sales@integrated-circuit.com



RHK003N06

Transistors

4V Drive Nch MOS FET **RHK003N06**

Structure

Silicon N-channel MOS FET

Features

- 1) Low On-resistance.
- 2) 4V drive.

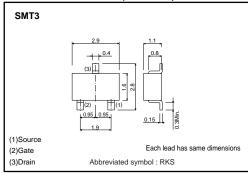
Applications

Switching

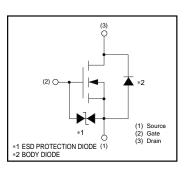
●Packaging specifications and hFE

	Package	Taping
Type	Code	T146
	Basic ordering unit (pieces)	3000
RHK003N06		0

●External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	Continuous	ID	±300	mA
Drain current	Pulsed	I _{DP} *1	±1.2	Α
Source current	Continuous	Is	200	mA
(Body diode)	Pulsed	I _{SP} *1	800	mA
Total power dissipation		P _D *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	625	°C/W

^{*} Each terminal mounted on a recommended land



^{*1} Pw≤10µs, Duty cycle≤1% *2 Each terminal mounted on a recommended land



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Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	_	±10	μА	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _(BR) DSS	60	-	_	٧	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	-	1	μА	V _{DS} = 60V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.5	٧	V _{DS} = 10V, I _D = 1mA
Static drain-source on-state		ı	0.7	1.0	Ω	I _D = 300mA, V _{GS} = 10V
resistance	R _{DS (on)} *	-	1.1	1.5	Ω	I _D = 300mA, V _{GS} = 4V
Forward transfer admittance	Y _{fs} *	0.2	-	_	S	V _{DS} = 10V, I _D = 300mA
Input capacitance	Ciss	-	33	_	pF	V _{DS} = 10V
Output capacitance	Coss	-	14	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	9	_	pF	f=1MHz
Turn-on delay time	td (on) *	-	6	_	ns	Vpp≒ 30V
Rise time	tr *	-	5	_	ns	I _D = 150mA V _G s= 10V
Turn-off delay time	td (off) *	-	13	_	ns	VGS= 10V RL=200Ω
Fall time	t _f *	-	80	_	ns	R _G =10Ω
Total gate charge	Qg *	_	3	6	nC	V _{DD} ≒30V
Gate-source charge	Qgs *	1	0.6	_	nC	Vgs= 10V
Gate-drain charge	Q _{gd} *	_	0.5	_	nC	ID= 300mA

^{*}Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	_	1.2	V	I _S = 300mA, V _{GS} =0V

^{*}Pulsed

Distributor of Rohm Semiconductor: Excellent Integrated System Limited

Datasheet of RHK003N06T146 - MOSFET N-CH 60V 300MA SOT-346

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

Appendix

Notes

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